

0105-50

0105-50 Information

	Part Number	0105-50	
Heisener.com		Microsemi Corporation	.
	Category	Discrete Semiconductor Products Transistors - Bipolar (BJT) - RF	
	Description	TRANS RF BIPO 140W 500MHZ 55JT2	- <u>20</u> 092
	Package	55JT	
		For the pricing/inventory/lead time, please contact	
For Reference Only		us Website: https://www.heisener.com E-mail: salesdept@heisener.com	Request a Quote

Certified Quality

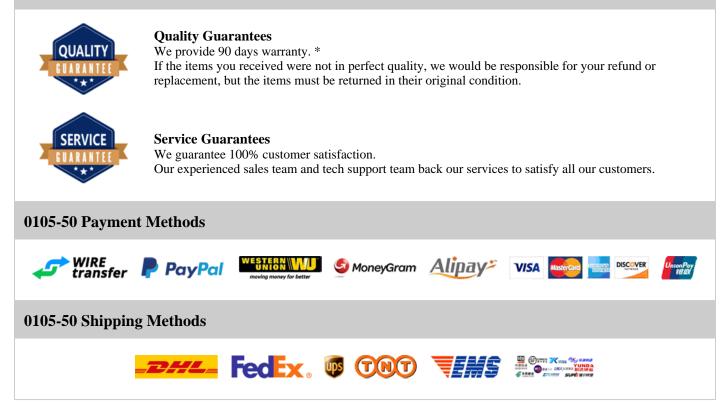
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0105-50 Specifications

Manufacturer Part Number0105-50ManufacturerMicrosemi CorporationCategoryDiscrete Semiconductor ProductsTransistors - Bipolar (BJT) - RFPackage55JTSeries-Transistor TypeNPNVoltage - Collector Emitter Breakdown (Max)65VFrequency - Transition100MHz ~ 500MHzNoise Figure (dB Typ @ f)-Gain8.5dB ~ 10dBPower - Max140WDC Current Gain (hFE) (Min) @ Ic, Vce10 @ 1A, 5VCurrent - Collector (Ic) (Max)7AOperating TemperatureConsis MountMounting TypeChassis MountPackage / Case55JTSupplier Device Package55JT			
CategoryDiscrete Semiconductor Products Transistors - Bipolar (BJT) - RFPackage55JTPackage-Series-Transistor TypeNPNVoltage - Collector Emitter Breakdown (Max)65VFrequency - Transition100MHz ~ 500MHzNoise Figure (dB Typ @ f)-Gain8.5dB ~ 10dBPower - Max140WDC Current Gain (hFE) (Min) @ Ic, Vce10 @ 1A, 5VOperating Temperature200°C (TJ)Mounting Type5JTPackage / Case5JTSupplier Device Package5ST	Manufacturer Part Number	0105-50	
Transistors - Bipolar (BJT) - RFPackage55JTSeries-Transistor TypeNPNVoltage - Collector Emitter Breakdown (Max)65VFrequency - Transition100MHz ~ 500MHzNoise Figure (dB Typ @ f)-Gain8.5dB ~ 10dBPower - Max140WDC Current Gain (hFE) (Min) @ Ic, Vce10 @ 1A, 5VCurrent - Collector (Ic) (Max)7AOperating Temperature200°C (TJ)Mounting Type55JTPackage / Case55JTSupplier Device Package55JT	Manufacturer	Microsemi Corporation	
Package55JTSeries-Transistor TypeNPNVoltage - Collector Emitter Breakdown (Max)65VFrequency - Transition100MHz ~ 500MHzNoise Figure (dB Typ @ f)-Gain8.5dB ~ 10dBPower - Max140WDC Current Gain (hFE) (Min @ Ic, Vce10 @ 1A, 5VCurrent - Collector (Ic) (Max)7AOperating Temperature200°C (TJ)Mounting Type5JTPackage / Case5JTSupplier Device Package5JT	Category	Discrete Semiconductor Products	
Series-Transistor TypeNPNVoltage - Collector Emitter Breakdown (Max)65VFrequency - Transition100MHz ~ 500MHzNoise Figure (dB Typ @ f)-Gain8.5dB ~ 10dBPower - Max140WDC Current Gain (hFE) (Min) @ Ic, Vce10 @ 1A, 5VCurrent - Collector (Ic) (Max)7AOperating TemperatureCoo°C (TJ)Mounting Type5JTSupplier Dackage5JT		Transistors - Bipolar (BJT) - RF	
Transistor TypeNPNVoltage - Collector Emitter Breakdown (Max)65VFrequency - Transition100MHz ~ 500MHzNoise Figure (dB Typ @ f)-Gain8.5dB ~ 10dBPower - Max140WDC Current Gain (hFE) (Min) @ Ic, Vce10 @ 1A, 5VCurrent - Collector (Ic) (Max)7AOperating Temperature200°C (TJ)Mounting Type5JTPackage / Case5JT	Package	55JT	
Voltage - Collector Emitter Breakdown (Max)65VFrequency - Transition100MHz ~ 500MHzNoise Figure (dB Typ @ f)-Gain8.5dB ~ 10dBPower - Max140WDC Current Gain (hFE) (Min) @ Ic, Vce10 @ 1A, 5VCurrent - Collector (Ic) (Max)7AOperating Temperature200°C (TJ)Mounting Type55JTPackage / Case55JT	Series	-	
Frequency - Transition100MHz ~ 500MHzFrequency - Transition-Noise Figure (dB Typ @ f)-Gain8.5dB ~ 10dBPower - Max140WDC Current Gain (hFE) (Min) @ Ic, Vce10 @ 1A, 5VCurrent - Collector (Ic) (Max)7AOperating Temperature200°C (TJ)Mounting Type5JTPackage / Case5JTSupplier Device Package5JT	Transistor Type	NPN	
Noise Figure (dB Typ @ f)-Gain8.5dB ~ 10dBPower - Max140WDC Current Gain (hFE) (Min) @ Ic, Vce10 @ 1A, 5VCurrent - Collector (Ic) (Max)7AOperating Temperature200°C (TJ)Mounting Type5JTPackage / Case5JTSupplier Device Package5JT	Voltage - Collector Emitter Breakdown (Max)	65V	
Gain8.5dB ~ 10dBPower - Max140WDC Current Gain (hFE) (Min) @ Ic, Vce10 @ 1A, 5VCurrent - Collector (Ic) (Max)7AOperating Temperature200°C (TJ)Mounting TypeChassis MountPackage / Case55JTSupplier Device Package55JT	Frequency - Transition	100MHz ~ 500MHz	
Power - Max140WDC Current Gain (hFE) (Min @ Ic, Yce10 @ 1A, 5VCurrent - Collector (Ic) (Max)7AOperating Temperature200°C (TJ)Mounting TypeChassis MountPackage / Case55JTSupplier Device Package55JT	Noise Figure (dB Typ @ f)	-	
DC Current Gain (hFE) (Min) @ Ic, Vce10 @ 1A, 5VCurrent - Collector (Ic) (Max)7AOperating Temperature200°C (TJ)Mounting TypeChassis MountPackage / Case55JTSupplier Device Package55JT	Gain	8.5dB ~ 10dB	
Current - Collector (Ic) (Max)7AOperating Temperature200°C (TJ)Mounting TypeChassis MountPackage / Case55JTSupplier Device Package55JT	Power - Max	140W	
Operating Temperature200°C (TJ)Mounting TypeChassis MountPackage / Case55JTSupplier Device Package55JT	DC Current Gain (hFE) (Min) @ Ic, Vce	10 @ 1A, 5V	
Mounting TypeChassis MountPackage / Case55JTSupplier Device Package55JT	Current - Collector (Ic) (Max)	7A	
Package / Case55JTSupplier Device Package55JT	Operating Temperature	200°C (TJ)	
Supplier Device Package 55JT	Mounting Type	Chassis Mount	
	Package / Case	55JT	
Report errors?	Supplier Device Package	55JT	
		Report errors?	

0105-50 Guarantees



If you have any question about 0105-50, please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com